

KMK830D

Advanced N-Ch Power MOSFET

SWITCHING REGULATOR APPLICATIONS

Features

• High Voltage : BV_{DSS}=500V(Min.)

• Low C_{rss} : C_{rss}=33pF(Typ.)

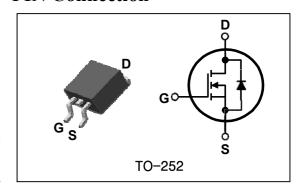
• Low gate charge : Qg=16nC(Typ.) • Low $R_{DS(on)}$: $R_{DS(on)}$ =1.5 Ω (Max.)

Ordering Information

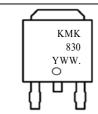
Type No.	Marking	Package Code
KMK830D	KMK830.	TO-252
	D 1'	•

. Dalian

PIN Connection



Marking Diagram



Column 1,2: Device Code

Column 3: Production Information

e.g.) YWW

-. YWW: Date Code (year, week)

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Absolute maximum ratings (T_C=25°C unless otherwise noted)

Characteristic	Characteristic Symbol		Rating	Unit
Drain-source voltage		V_{DSS}	500	V
Gate-source voltage		V_{GSS}	±30	V
Drain current (DC) *	I_{D}	(Tc=25℃)	4.5	Α
Drain current (DC)	1 _D	(Tc=100°C)	2.9	Α
Drain current (Pulsed) *		I_{DM}	18	Α
Power dissipation		P_D	48	W
Avalanche current (Single) 2		I_{AS}	4.5	Α
Single pulsed avalanche energy ②		E _{AS}	250	mJ
Avalanche current (Repetitive) 1		${ m I}_{\sf AR}$	4.5	Α
Repetitive avalanche energy ①		E _{AR}	5.0	mJ
Junction temperature		Tյ	150	°C
Storage temperature range		T_{stg}	-55~150	C

^{*} Limited by maximum junction temperature

Characteristic		Symbol	Typ.	Max.	Unit
Thermal	Junction-case	$R_{th(\mathtt{J-C})}$	-	2.6	°C/W
resistance	Junction-ambient **	$R_{th(J-A)}$	ı	50	- C/ W

^{**} When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	I _D =250uA, V _{GS} =0	500	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250uA$, $V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source cut-off current	I_{DSS}	V _{DS} =500V, V _{GS} =0V	-	-	1	uA
Gate leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±30V	-	-	±100	nA
Drain-source on-resistance 4	R _{DS(ON)}	V _{GS} =10V, I _D =2.25A	-	1.2	1.5	^
Forward transfer conductance ④	g _{fs}	V _{DS} =10V, I _D =2.25A	-	5.2	-	S
Input capacitance	Ciss		-	745	930	
Output capacitance	Coss	$V_{GS}=0V$, $V_{DS}=25V$, $V_{DS}=25V$	-	82	102	pF
Reverse transfer capacitance	Crss		-	33	42	
Turn-on delay time	t _{d(on)}		-	12	-	
Rise time	t _r	$V_{DD} = 250V, I_{D} = 4.5A$ $R_{G} = 25\Omega$	-	46	-	nc
Turn-off delay time	t _{d(off)}	34	-	50	-	ns
Fall time	t _f		-	48	-	
Total gate charge	Qg	V -400V V -10V	-	16	20	
Gate-source charge	Q_{gs}	V_{DS} =400V, V_{GS} =10V I_{D} =4.5A	-	5.5	-	nC
Gate-drain charge	Q_{gd}	34	_	4.0	-	

Source-Drain Diode Ratings and Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I _S	Integral reverse diode	-	-	4.5	Α
Source current (Pulsed)	1 I _{SM}	in the MOSFET	-	1	18	A
Forward voltage	V _{SD}	V _{GS} =0V, I _S =4.5A	-	ı	1.4	٧
Reverse recovery time	t _{rr}	I _S =4.5A, V _{GS} =0V	-	263	ı	ns
Reverse recovery charge	Q _{rr}	dI _F /dt=100A/us	-	1.9	-	uC

Note;

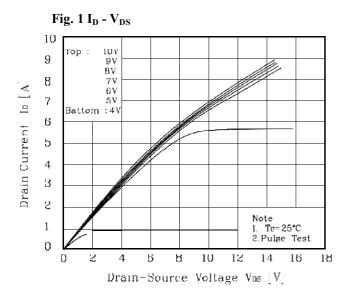
1 Repetitive rating: Pulse width limited by maximum junction temperature

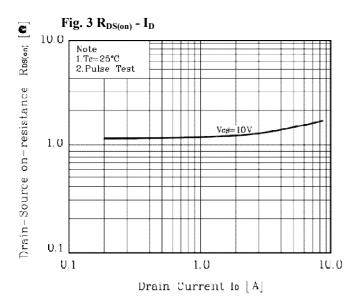
② L=22.2mH, I_{AS} =4.5A, V_{DD} =50V, R_{G} =25 Ω , Starting T_{J} =25 $^{\circ}$ C

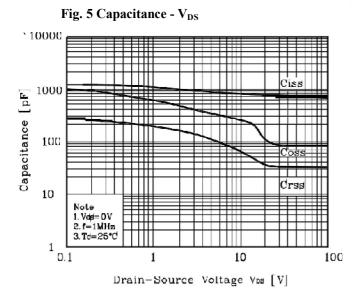
③ Pulse Test : Pulse width≤300us, Duty cycle≤2%

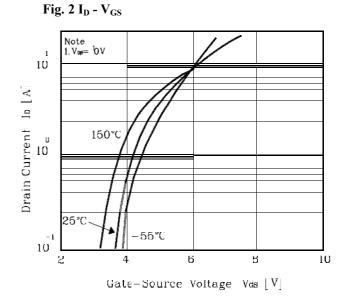
4 Essentially independent of operating temperature

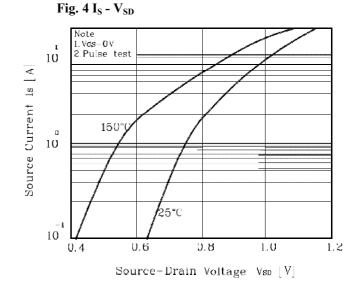
Electrical Characteristic Curves

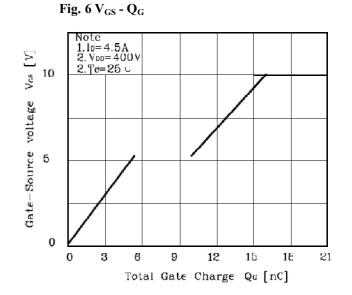












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Fig. 7 $V_{(BR)DSS}$ - T_J

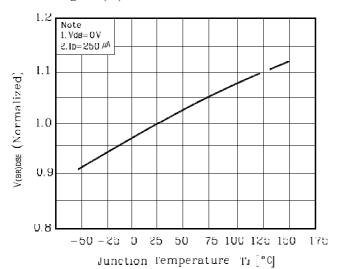


Fig. 8 $R_{DS(on)}$ - T_J

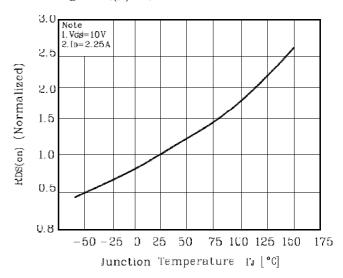


Fig. 9 I_D - T_C

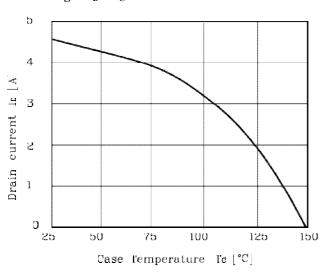


Fig. 10 Safe Operating Area

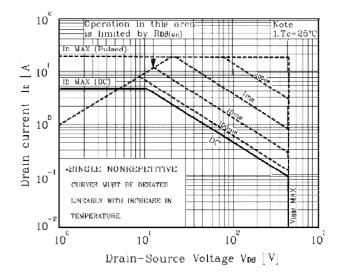


Fig. 11 Gate Charge Test Circuit & Waveform

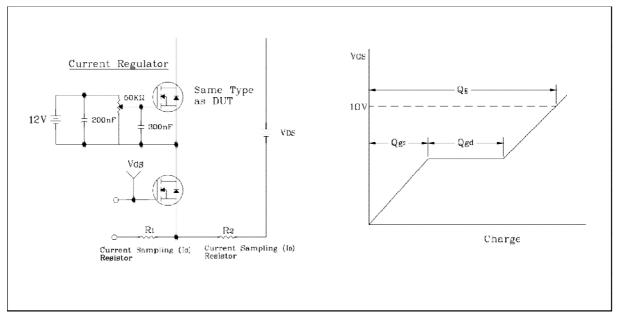


Fig. 12 Resistive Switching Test Circuit & Waveform

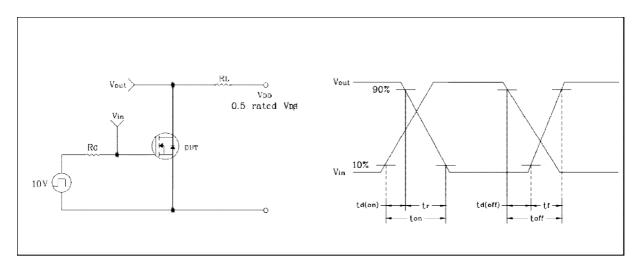


Fig. 13 E_{AS} Test Circuit & Waveform

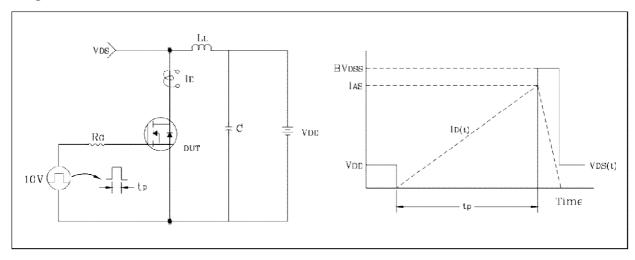
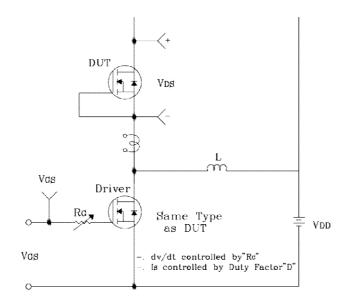
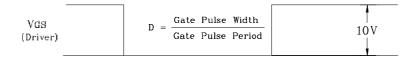
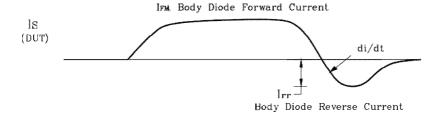
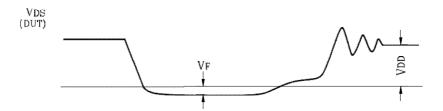


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



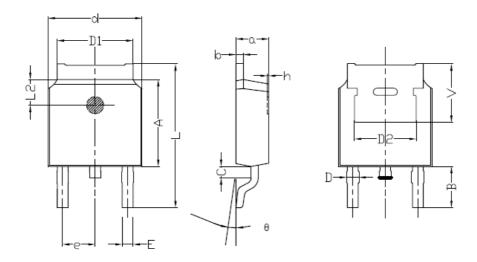






Outline Dimension

unit: mm



C 1 1	Dimensions I	n Millimeters	Dimensions	In Inches	
Symbol	min.	max.	min.	max.	
a	2. 20	2. 40	0.087	0.095	
b	0.46	0. 58	0.018	0.023	
С	0.70	0. 90	0.028	0.035	
D	0.80	1.00	0.032	0.039	
d	6. 30	6. 70	0.248	0.264	
D1	5. 00	5. 50	0. 197	0. 217	
D2	TY	P 4.83	TYP 0.190		
Α	5.80	6. 20	0.228	0. 244	
е	2. 19	2. 39	0.086	0.094	
L	9. 40	10. 40	0.370	0.409	
В	2.6	3. 2	0. 102	0.126	
L2	1. 5	1. 8	0.059	0.071	
θ	0	8	0	8	
h	0	0. 3	0	0.012	
V	5. 25	5. 85	0. 207	0. 230	
Е	0.6	0.8	0. 024	0.032	

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